

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	4.2Ω@10V	170mA
	4.3Ω@4.5V	

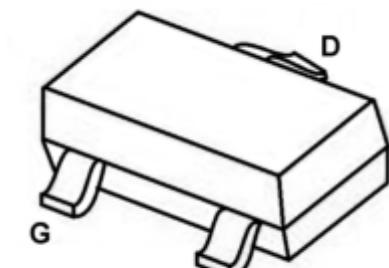
Feature

- Advanced trench cell design
- High speed switch
- ESD Protected, HBM ≥ 2 KV

Application

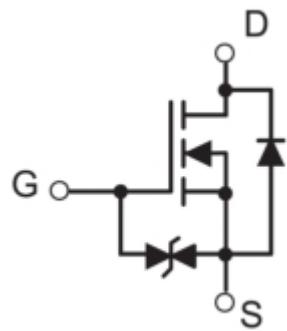
- Portable appliances
- Load switch appliances

Package

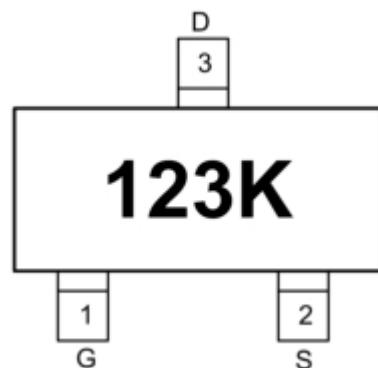


SOT-23

Circuit diagram



Marking



Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	170	mA
Power Dissipation	P_D	0.35	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$



ZL MOSFET

BSS123K

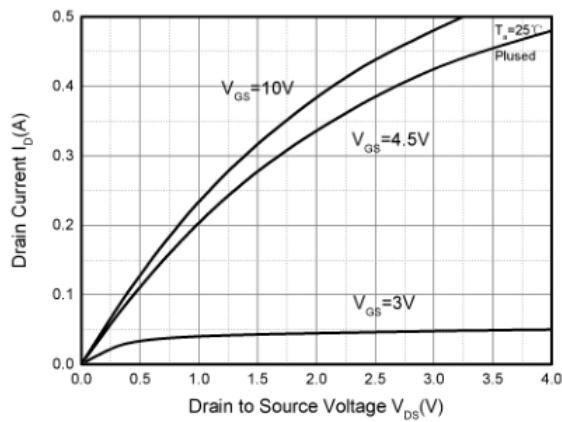
Electrical characteristics

(T_A=25°C, unless otherwise noted)

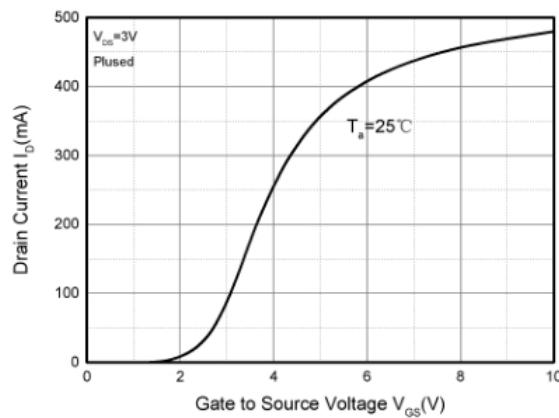
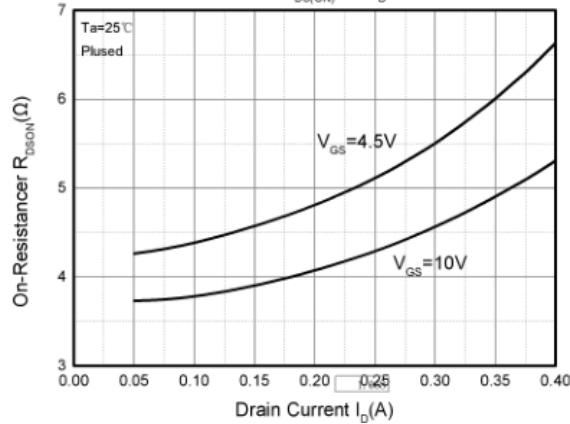
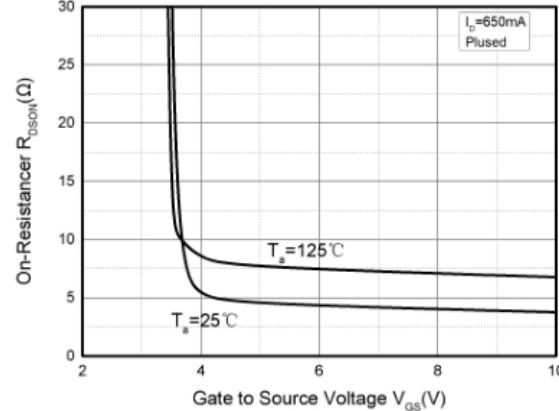
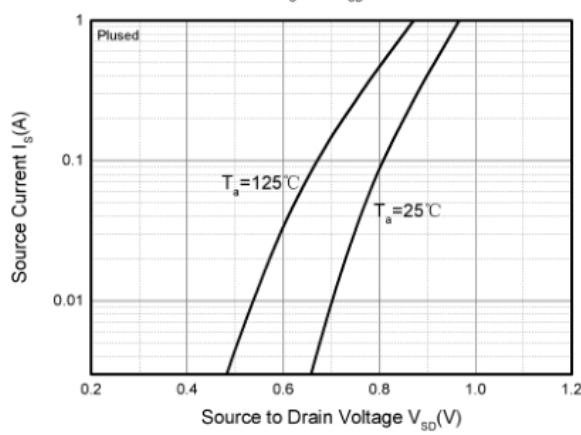
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100			V
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.3	1.7	2.5	V
Gate-body leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±10	uA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 80V, V _{GS} = 0V			1	uA
Drain-source on-resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 250mA		4	6	Ω
		V _{GS} = 4.5V, I _D = 200mA		4.3	9	
Dynamic characteristics						
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =10V, I _D =220mA			2	nC
Gate-Source Charge	Q _{gs}				0.25	
Gate-Drain Charge	Q _{gd}				0.4	
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHz			60	pF
Output Capacitance	C _{oss}				15	
Reverse Transfer Capacitance	C _{rss}				6	
Switching Characteristics						
Turn-on delay time	t _{d(on)}	V _{DD} =30V, V _{GS} =10V, I _D =-280mA, R _G =50Ω			8	ns
Turn-On Rise Time	t _r				8	
Turn-off delay time	t _{d(off)}				13	
Turn-Off Fall Time	t _f				16	
Source-Drain Diode Characteristics						
Diode Forward voltage	V _{SD}	V _{GS} = 0V, I _S =400mA			1.3	V

Typical Characteristics

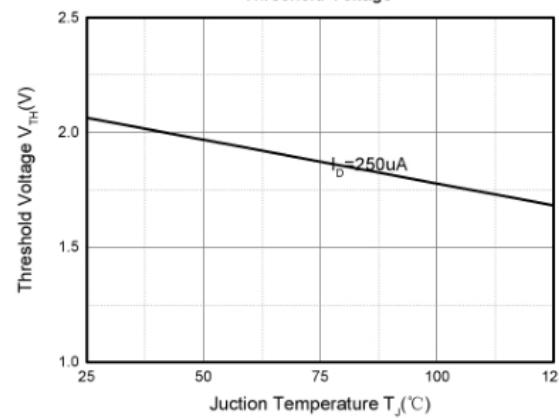
Output Characteristics



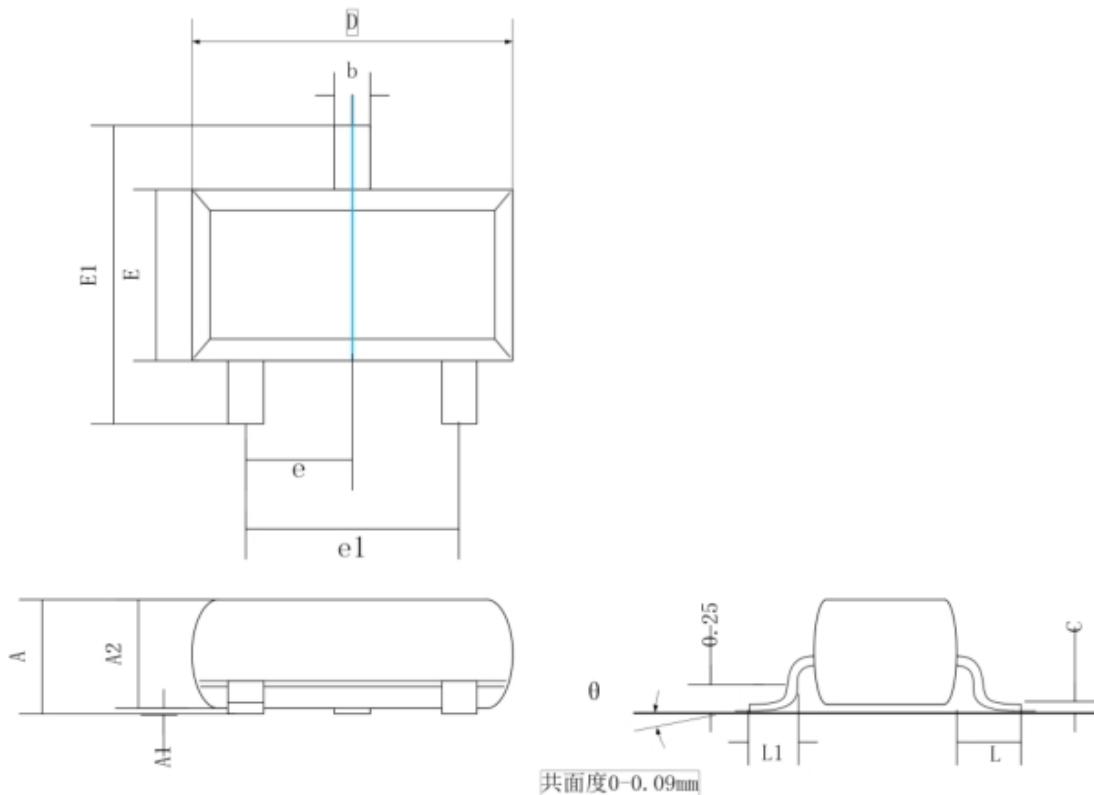
Transfer Characteristics

 $R_{DS(ON)} - I_D$  $R_{DS(ON)} - V_{GS}$  $I_S - V_{SD}$ 

Threshold Voltage



SOT-23 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50
θ	0°	8°